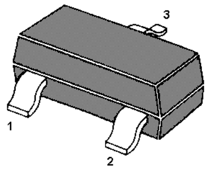
MMBTSC3324

NPN Silicon Epitaxial Planar Transistor

for audio frequency low noise amplifier applications.

The transistor is subdivided into two groups G and L, according to its DC current gain.



1. Base 2. Emitter 3. Collector

SOT-23 Plastic Package

Absolute Maximum Ratings (T_a = 25 °C)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	120	V
Collector Emitter Voltage	V_{CEO}	120	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Base Current	I_B	20	mA
Collector Power Dissipation	P_{tot}	200	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	- 55 to + 125	°C

Characteristics at T_a=25 °C

Parameter		Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at V_{CE} = 6 V, I_C = 2 mA	G	h_{FE}	200	-	400	-
	L	h_{FE}	350	-	700	-
Collector Base Cut-off Current at V_{CB} = 120 V		I_{CBO}	-	-	0.1	µA
Emitter Base Cut-off Current at V_{EB} = 5 V		I_{EBO}	-	-	0.1	µA
Collector Emitter Saturation Voltage at I_C = 10 mA, I_B = 1 mA		$V_{CE(sat)}$	-	-	0.3	V
Transition Frequency at V_{CE} = 6 V, I_C = 1 mA		f_T	-	100	-	MHz
Collector Output Capacitance at V_{CB} = 10 V, f = 1 MHz		C_{ob}	-	4	-	pF

TOP DYNAMIC

ISO14001 : 2004
Certificate No. 121505007
ISO 9001 : 2008
Certificate No. 50114012
OHSAS 18001 : 2007
Certificate No. 05131506006
IECQ QC 080000
Certificate No. IECQ-H MOODY 14.0022

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